



Low Voltage, Dual DPDT and Quad SPDT Analog Switches

DESCRIPTION

The DG2018 and DG2019 are low voltage, single supply analog switches. The DG2018 is a dual double-pole/double-throw (DPDT) with two control inputs that each controls a pair of single-pole/double-throw (SPDT). The DG2019 uses one control pin to operate four independent SPDT switches.

When operated on a + 3 V supply, the DG2018's control pins are compatible with 1.8 V digital logic. The DG2019 has an available feature of a V_L pin that allows a 1.0 V threshold for the control pin when V_L is powered with 1.5 V.

Built on Vishay Siliconix's low voltage submicron CMOS process, the DG2018 and DG2019 are ideal for high performance switching of analog signals; providing low onresistance (6 Ω at + 2.7 V), fast speed (T_{on} , T_{off} at 42 ns and 16 ns), and a bandwidth that exceeds 180 MHz.

The DG2018 and DG2019 were designed to offer solutions that extend beyond audio/video functions, to providing the performance required for today's demanding mixed-signal switching in portable applications.

An epitaxial layer prevents latch-up. Brake-before-make is guaranteed for all SPDT's. All switches conduct equally well in both directions when on, and blocks up to the power supply level when off.

DG2018DN

FEATURES

- Low voltage operation (1.8 V to 5.5 V)
- · Low on resistance
 - R_{DS(on)}: 6 Ω at 2.7 V
- · Low voltage logic compatible
 - DG2019: V_{INH} = 1 V
- · High bandwidth: 180 MHz
- · QFN-16 package

BENEFITS

- · Ideal for both analog and digital signal switching
- Reduced power consumption
- High accuracy
- · Reduced PCB space
- · Fast switching
- Low leakage

APPLICATIONS

- · Cellular phones
- · Audio and video signal routing
- · PCMCIA cards
- · Battery operated systems
- · Portable instrumentation

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

QFN-16 (3 X 3) V+ COM1 NO1 NC4 15 14 13 16 NC₁ COM4 NO4 IN1, IN2 NO₂ IN3, IN4 COM₂ NC3 NO3 COM3 GND Top View

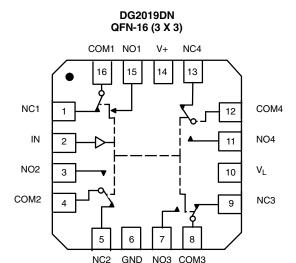
TRUTH TABLE					
IN1, IN2					
Logic	NC1 and NC2	NO1 and NO2			
0	ON	OFF			
1	OFF	ON			
IN3, IN4					
Logic	NC3 and NC4	NO3 and NO4			
0	ON	OFF			
1	OFF	ON			

ORDERING INFORMATION					
Temp. Range	Package	Part Number			
- 40 °C to 85 °C	QFN-16 (3 x 3 mm)	DG2018DN			

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FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Top View

TRUTH TABLE					
Logic	NC1, 2, 3 and 4	NO1, 2, 3 and 4			
0	ON	OFF			
1	OFF	ON			

ORDERING INFORMATION				
Temp. Range	Package	Part Number		
- 40 °C to 85 °C	QFN-16 (3 x 3 mm)	DG2019DN		

ABSOLUTE MAXIMUM RATINGS						
Parameter		Limit	Unit			
Reference V+ to GND	- 0.3 to + 6	V				
IN, COM, NC, NO	- 0.3 to (V+ + 0.3)	v				
Continuous Current (Any terminal)	± 50	mA				
Peak Current (Pulsed at 1 ms, 10 % Duty Cycle)		± 100				
Storage Temperature (D Suffix)		- 65 to 150	°C			
Power Dissipation (Packages) ^b	QFN-16 (3 x 3 mm) ^c	850	mW			

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.
- c. Derate 4.0 mW/°C above 70 °C.





		Test Conditions				Limits		
		Otherwise Unless Specified V+ = 3 V, ± 10 %,			- 40	°C to 85	°C	
		$V + = 3 V, \pm 10 \%,$ (DG2018 Only) $V_{IN} = 0.5 \text{ or } 1.$.4 V ^e					
Parameter	Symbol	(DG2019 Only) $V_L = 1.5 \text{ V}, V_{IN} = 0.4$		Temp.a	Min.b	Typ. ^c	Max.b	Unit
Analog Switch	O y S O.	77 E 7 IIV		. ср.		.,,	ı ınıaxı	
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}			Full	0		V+	V
On-Resistance	R _{ON}	$V+ = 2.7 \text{ V}, V_{COM} = 0.2 \text{ V}/1.9$ $I_{NO}, I_{NC} = 10 \text{ mA}$	5 V	Room Full		6	12 15	
R _{ON} Flatness	R _{ON} Flatness	V+ = 2.7 V		Room		0.5	2	Ω
R _{ON} Match Between Channels	ΔR _{ON}	$V_{COM} = 0 \text{ to V+, } I_{NO}, I_{NC} = 10$) mA	Room		0.6	3	1
Switch Off Leakage Current	$I_{NO(off)}$ $I_{NC(off)}$	$V+ = 3.3 \text{ V}, V_{NO}, V_{NC} = 0.3 \text{ V}$	/3 V	Room Full	- 1 - 10	0.3	1 10	
omion on Esanago ourion	I _{COM(off)}	$V_{COM} = 3 \text{ V}/0.3 \text{ V}$		Room Full	- 1 - 10	0.3	1 10	nA
Channel-On Leakage Current	I _{COM(on)}	$V+ = 3.3 V, V_{NO}, V_{NC} = V_{COM} = 0$.3 V/3 V	Room Full	- 1 10	0.3	1 10	
Digital Control			T = =	1			Т	
Input High Voltage	V_{INH}	V - 1 5 V	DG2018	Full	1.4			
		V _L = 1.5 V	DG2019 DG2018	Full Full	1.0		0.5	V
Input Low Voltage	V_{INL}	V _L = 1.5 V	DG2018 DG2019	Full			0.3	-
Input Capacitance	C _{in}	f = 1 MHz		Full		9		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+		Full	- 1		1	μΑ
Dynamic Characteristics							L	
Turn-On Time	t _{ON}	V_{NO} or V_{NC} = 2.0 V, R_L = 300 Ω , C_L = 35 pF		Room Full		42	55 65	
Turn-Off Time	t _{OFF}			Room Full		16	25 35	ns
Break-Before-Make Time	t _d	V_{NO} or V_{NC} = 2.0 V, R_L = 50 Ω , C_L		Full	1			
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} =$	= 0 Ω	Room		- 1.46		рC
Off-Isolation ^d	OIRR			Room		- 67		dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$		Room		- 72		ub
Bandwidth ^d	BW			Room		180		MHz
N. N. Off Canacitanas ^d	C _{NO(off)}	V _{IN} = 0 or V+, f = 1 MHz		Room		9		
N _O , N _C Off Capacitance ^d	C _{NC(off)}			Room		9		pF
Channel-On Capacitance ^d	C _{NO(on)}			Room		30		
•	C _{NC(on}			Room		30		
Power Supply				1			1	
Power Supply Current	l+	$V_{IN} = 0 \text{ or } V+$		Full		0.01	1.0	μΑ

Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
 c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.

DG2018, DG2019

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S-82626-Rev. C, 03-Nov-08

SPECIFICATIONS V+	= 5 V							
		Test Conditions Otherwise Unless Specified V+ = 5 V, ± 10 %,			- 40	Limits 0 °C to 85	5°C	
		(DG2018 Only) V _{IN} = 0.8 or 1	I.8 V ^e					
Parameter	Symbol	(DG2019 Only) V _L = 1.5 V, V _{IN} = 0		Temp.a	Min.b	Typ. ^c	Max.b	Unit
Analog Switch							l.	
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}			Full	0		V+	V
On-Resistance	R _{ON}	$V+ = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC}$	= 10 mA	Room Full		4	8 10	
R _{ON} Flatness	R _{ON} Flatness	$V_{+} = 4.5 V$ $V_{COM} = 0 \text{ to } V_{+}, I_{NO}, I_{NC} = 10$	0 mA	Room		0.6	1.2	Ω
R _{ON} Match Between Channels	ΔR_{ON}	VCOM = 0 to V+, INO, INC = 10	OTIA	Room		0.6	1.2	
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 5.5 V		Room Full	- 1 - 10	0.03	1 10	nA
Switch On Leakage Guirent	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V}/4.5 \text{ V}$, $V_{COM} = 4$	5 V/1 V	Room Full	- 1 - 10	0.03	1 10	
Channel-On Leakage Current ^f	I _{COM(on)}	$V+ = 5.5 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 10$	1 V/4.5 V	Room Full	- 1 - 10	0.03	1 10	
Digital Control	T		T			ı	ı	ı
Input High Voltage	V _{INH}	V _L = 1.5 V	DG2018 DG2019	Full Full	1.8			.,
Input Low Voltage	V		DG2018	Full			0.8	V
Input Low Voltage	V _{INL}	V _L = 1.5 V	DG2019	Full			0.4	
Input Capacitance	C _{in}			Full		9		pF
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ or } V+$		Full	1		1	μΑ
Dynamic Characteristics	1					1	1	ı
Turn-On Time	t _{ON}	V_{NO} or V_{NC} = 3 V, R_L = 300 Ω, C	_I = 35 pF	Room Full		44	48 52	
Turn-Off Time	t _{OFF}		-	Room Full		19	33 35	ns
Break-Before-Make Time	t _d	V_{NO} or $V_{NC} = 3 \text{ V}$, $R_L = 50 \Omega$, C_L		Full	1			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN}$	= 0 Ω	Room		- 2.46		рC
Off-Isolation ^d	OIRR			Room		- 67		dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega, C_L = 5 pF, f = 1 N$	ИHz	Room		- 72		3.5
Bandwidth ^d	BW			Room		180		MHz
Source-Off Capacitanced	C _{NO(off)}			Room		7.5		
Oddioc-On Oapaditarioc	C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz		Room		7.5		pF
Channel-On Capacitanced	C _{NO(on)}			Room		30		ļ .
·	C _{NC(on}			Room		30		
Power Supply	1	l				1		
Power Supply Range	V+			- ··	1.8	0.01	5.5	V
Power Supply Current	l+	$V_{IN} = 0 \text{ or } V+$		Full		0.01	1.0	μΑ

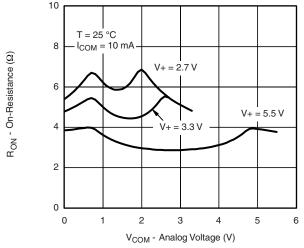
Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Not production tested.

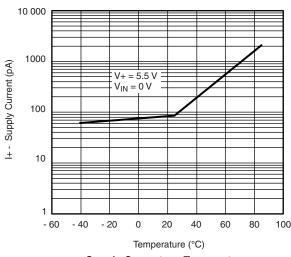
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



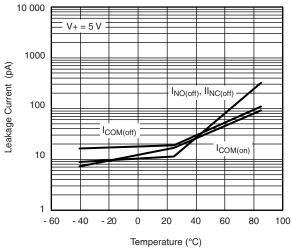
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



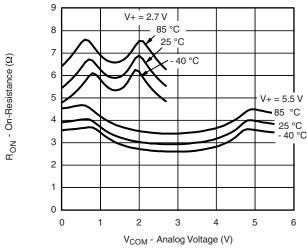
 R_{ON} vs. V_{COM} and Supply Voltage



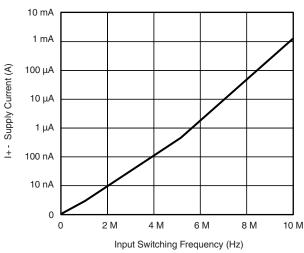
Supply Current vs. Temperature



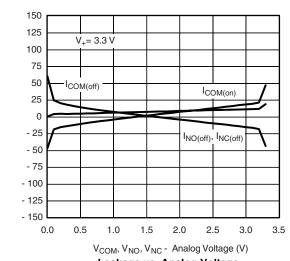
Leakage Current vs. Temperature



R_{ON} vs. Analog Voltage and Temperature

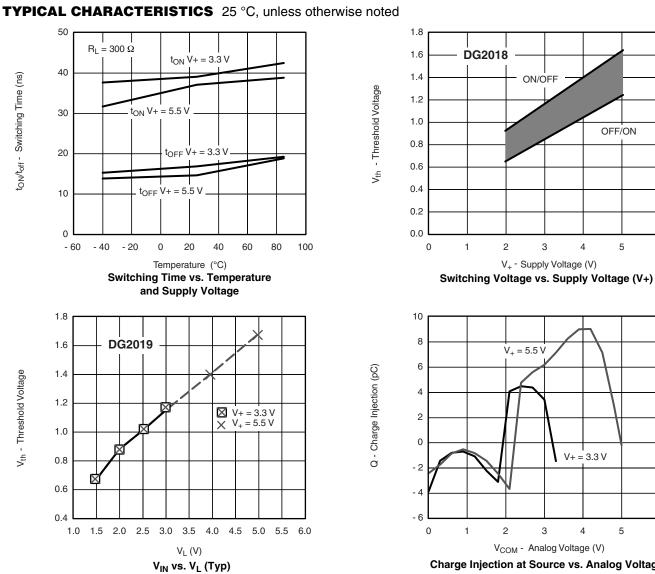


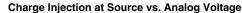
Supply Current vs. Input Switching Frequency

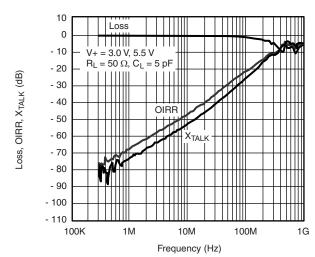


Leakage Current (pA)

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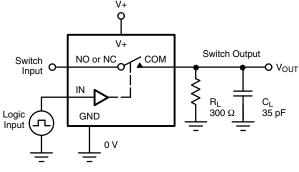




Insertion Loss, Off Isolation and Crosstalk vs. Frequency

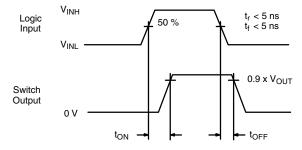


TEST CIRCUITS



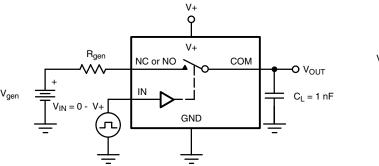
 $\boldsymbol{C}_{\boldsymbol{L}}$ (includes fixture and stray capacitance)

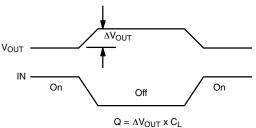
$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

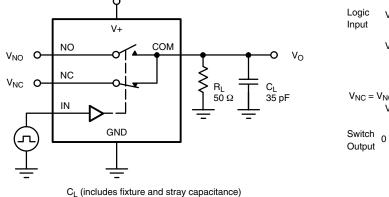
Figure 1. Switching Time





IN depends on switch configuration: input polarity determined by sense of switch.

Figure 2. Charge Injection



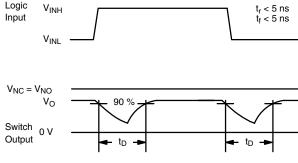


Figure 3. Break-Before-Make Interval

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TEST CIRCUITS



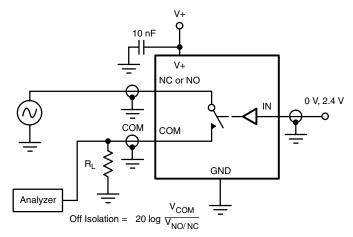


Figure 4. Off-Isolation

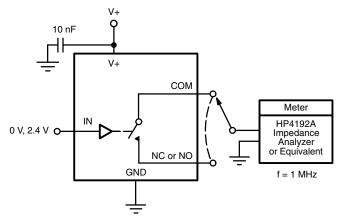


Figure 5. Channel Off/On Capacitance

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